2SC5023

Silicon NPN Epitaxial

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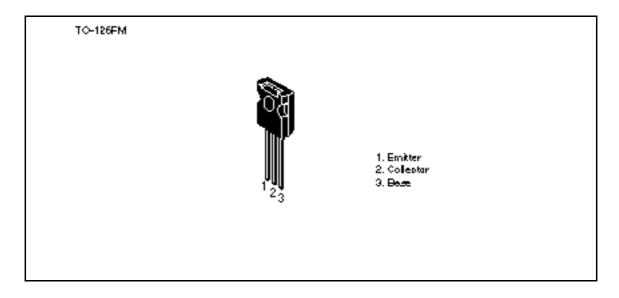
Application

High frequency amplifier

Features

- Excellent high frequency characteristics $f_T = 1000 \text{ MHz}$ typ
- High breakdown voltage and low output capacitance V_{CEO} = 100 V, Cob = 4.5 pF typ
- Suitable for wide band video amplifier

Outline





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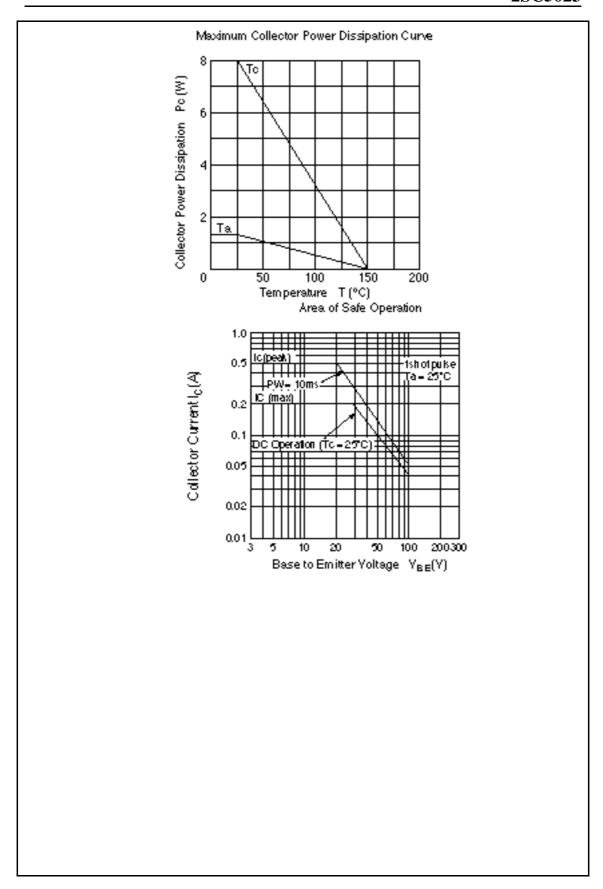
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V _{CEO}	100	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	0.2	A
Collector peak current	I _{C (peak)}	0.5	A
Collector power dissipation	P _c	1.25	W
	P _c *1	8	_
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value at $T_c = 25$ °C.

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item		Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage		$V_{(BR)CBO}$	100	_	_	V	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$
Collector to emitt voltage	er breakdown	$V_{(BR)CEO}$	100	_	_	V	$I_C = 1 \text{ mA}, R_{BE} =$
Collector cutoff c	urrent	I _{CBO}	_	_	1.0	μΑ	$V_{CB} = 80 \text{ V}, I_{E} = 0$
Emitter cutoff cur	rent	I _{EBO}	_	_	10	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
DC current	2SC5023B	h _{FE}	60	_	120		$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$
transfer ratio	2SC5023C	h _{FE}	100	_	200		
Base to emitter v	oltage	V_{BE}	_	_	1.0	V	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{ mA}$
Collector to emitt voltage	er saturation	$V_{\text{CE (sat)}}$	_	_	1.0	V	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$
Gain bandwidth product		f _T	800	1000	_	MHz	$V_{CE} = 20 \text{ V}, I_{C} = 100 \text{ mA}$
Collector output capacitance		Cob	_	4.5	6.0	pF	$V_{CB} = 30 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$



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